Towards Highly Efficient Thermally Activated Delayed Fluorescence Devices through a Trap-assisted Recombination Mechanism and Reduced Interfacial Excitons Annihilation

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Fig. S1 The PL spectra of doped films for 3-CzTHZ: 6 wt% 4CzPN and 5-CzTHZ: 6 wt% 4CzPN.

Fig. S2 EQE-current density properties of devices A and B hosted by 3-CzTHZ and 5-CzTHZ, respectively.
Fig. S3 EL spectra of two devices by inserting an ultrathin (fbii)Ir(acac) sensor layer closed to the ETL side.

Fig. S4 EL spectra of two devices by inserting an ultrathin (fbii)Ir(acac) sensor layer in the middle of the EML.